



50V NPN SMALL SIGNAL TRANSISTOR IN DFN1006

Features

- BV_{CEO} > 50V
- I_C = 100mA High Collector Current
- P_D = 1000mW Power Dissipation
- 0.60mm² Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type 2DA1774QLP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free, "Green" Device (Note 3)
- Qualified to AEC-Q101Standards for High Reliability

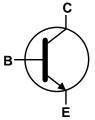
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu.
 Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0009 grams (Approximate)

X1-DFN1006-3







Device Symbol



Top View Device Schematic

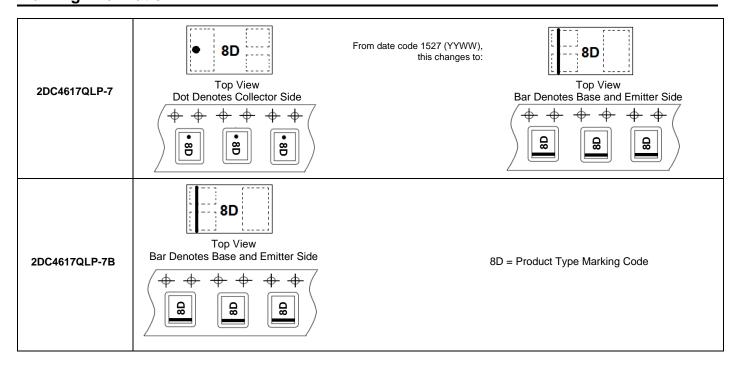
Ordering Information (Note 4)

| Product | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|---------------|---------|--------------------|-----------------|-------------------|
| 2DC4617QLP-7 | 8D | 7 | 8 | 3,000 |
| 2DC4617QLP-7B | 8D | 7 | 8 | 10,000 |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information





Absolute Maximum Ratings ($@T_A = +25^{\circ}C$ unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage | V_{CBO} | 50 | V |
| Collector-Emitter Voltage | V _{CEO} | 50 | V |
| Emitter-Base Voltage | V_{EBO} | 5.0 | V |
| Collector Current | lc | 100 | mA |
| Peak Collector Current | I _{CM} | 200 | mA |

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|-----------------------------------|----------------|------|------|--|
| Power Dissipation | (Note 5) | D | 400 | - mW | |
| Fower Dissipation | (Note 6) | P _D | 1000 | | |
| Thermal Resistance, Junction to Ambient | (Note 5) | 6 | 310 | °C/W | |
| Thermal Resistance, Junction to Ambient | (Note 6) | $R_{	hetaJA}$ | 120 | | |
| Thermal Resistance, Junction to Lead (Note 7) | | $R_{	heta JL}$ | 120 | °C/W | |
| Operating and Storage and Temperature Range | T _J , T _{STG} | -55 to +150 | °C | | |

ESD Ratings (Note 8)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 200 | V | В |

Electrical Characteristics @TA = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Max | Unit | Test Condition |
|--------------------------------------|----------------------|-----|-----|------|--|
| OFF CHARACTERISTICS (Note 9) | | | | | |
| Collector-Base Breakdown Voltage | BV _{CBO} | 50 | _ | V | $I_C = 50\mu A, I_E = 0$ |
| Collector-Emitter Breakdown Voltage | BV _{CEO} | 50 | _ | V | $I_C = 1.0 \text{mA}, I_B = 0$ |
| Emitter-Base Breakdown Voltage | BV _{EBO} | 5.0 | _ | V | $I_E = 50 \mu A, I_C = 0$ |
| Collector Cutoff Current | | _ | 100 | nA | V _{CB} = 30V |
| Collector Cuton Current | ICBO | | 5 | μΑ | $V_{CB} = 30V, T_A = +150^{\circ}C$ |
| Emitter Cutoff Current | I _{EBO} | _ | 100 | nA | V _{EB} = 4.0V |
| ON CHARACTERISTICS (Note 9) | | | | | |
| DC Current Gain | h _{FE} | 120 | 270 | _ | $V_{CE} = 6.0V, I_{C} = 1.0mA$ |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | _ | 0.2 | V | $I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$ |
| SMALL SIGNAL CHARACTERISTICS | | | | | |
| Output Capacitance | C _{obo} | _ | 3.5 | pF | $V_{CB} = 12V, f = 1.0MHz, I_{E} = 0$ |
| Current Gain-Bandwidth Product | f⊤ | 100 | _ | MHz | $V_{CE} = 12V, I_{C} = 2.0mA,$ f = 100MHz |

Notes:

- For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

- 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

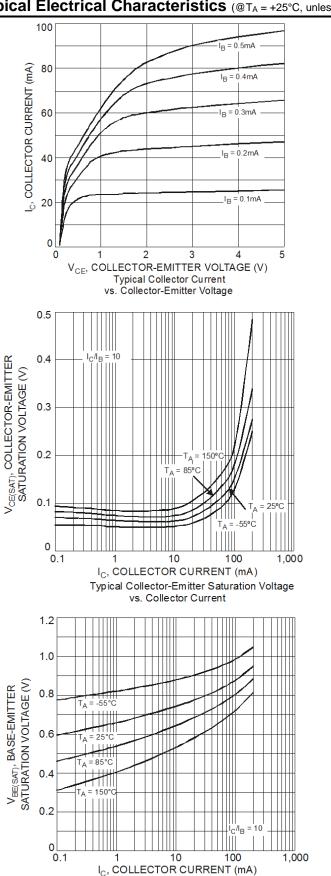
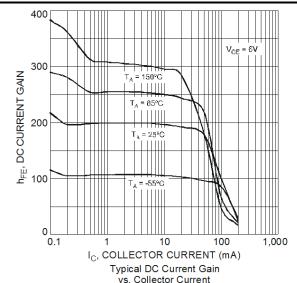
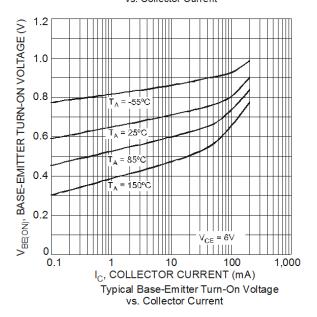


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

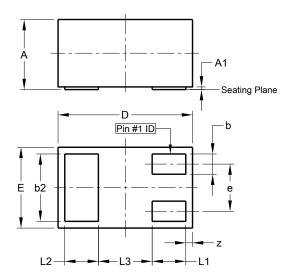






Package Outline Dimensions

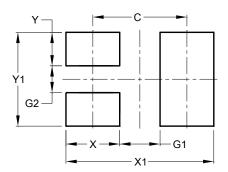
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| X1-DFN1006-3 | | | | |
|----------------------|------|-------|------|--|
| Dim | Min | Max | Тур | |
| Α | 0.47 | 0.53 | 0.50 | |
| A1 | 0.00 | 0.05 | 0.03 | |
| b | 0.10 | 0.20 | 0.15 | |
| b2 | 0.45 | 0.55 | 0.50 | |
| D | 0.95 | 1.075 | 1.00 | |
| Е | 0.55 | 0.675 | 0.60 | |
| е | ı | - | 0.35 | |
| L1 | 0.20 | 0.30 | 0.25 | |
| L2 | 0.20 | 0.30 | 0.25 | |
| L3 | - | - | 0.40 | |
| Z | 0.02 | 0.08 | 0.05 | |
| All Dimensions in mm | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 0.70 | | |
| G1 | 0.30 | | |
| G2 | 0.20 | | |
| X | 0.40 | | |
| X1 | 1.10 | | |
| Y | 0.25 | | |
| Y1 | 0.70 | | |



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